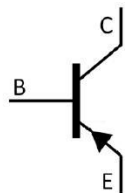


Silicon PNP transistor in a SOT-323 Plastic Package.

Complements the MMBTA06W.

General purpose amplifier.



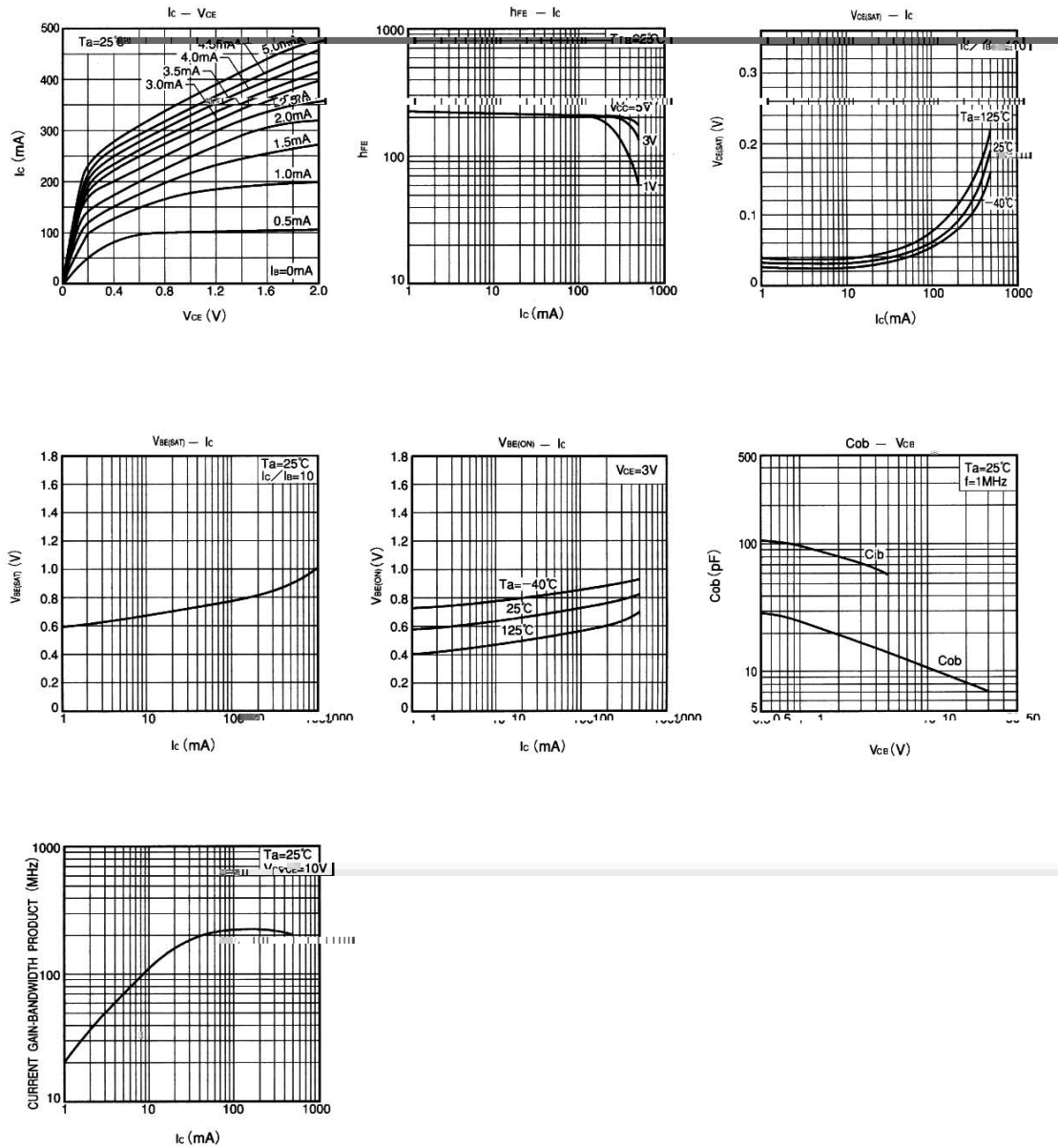
PIN1 Emitter PIN 2 Base PIN 3 Collector

h_{FE} Range	>100
Marking	HR2G

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-80	V
Collector to Emitter Voltage	V_{CEO}	-80	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-0.5	A
Collector Power Dissipation	P_C	150	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55~150	

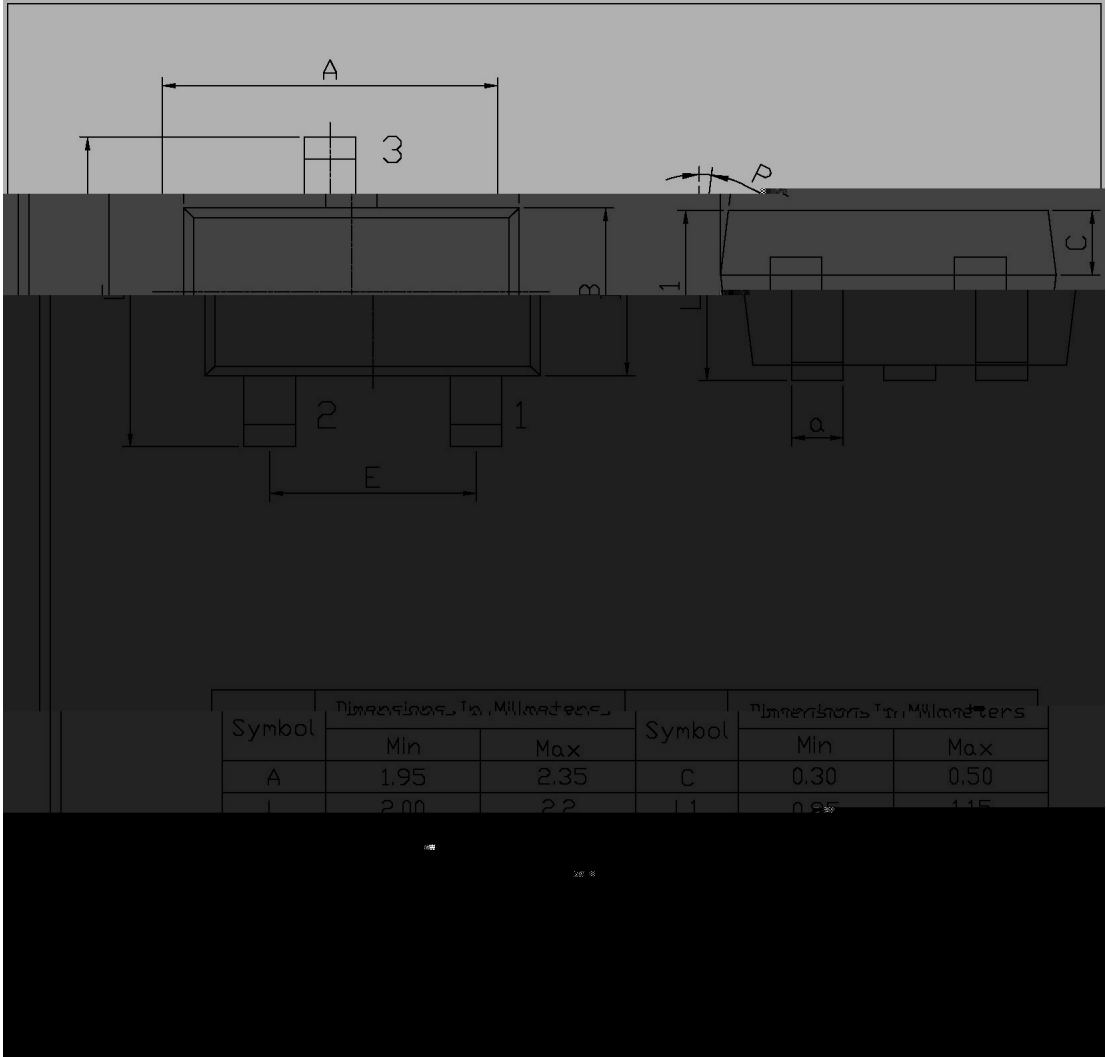
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C = -100\text{ A}$ $I_E = 0$	-80			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C = -1.0\text{mA}$ $I_B = 0$	-80			V
Collector Cut-Off Current	I_{CBO}	$V_{CB} = -80\text{ V}$ $I_E = 0$			-0.1	A
Emitter Cut-Off Current	I_{CEO}	$V_{CB} = -60\text{ V}$ $I_B = 0$			-1.0	A
Emitter Base Cut-Off Current	I_{EBO}	$V_{BE} = -4.0\text{V}$ $I_C = 0$			-0.1	A
DC Current Gain	$h_{FE(1)}$	$V_{CE} = -1.0\text{V}$ $I_C = -100\text{mA}$	100			
	$h_{FE(2)}$	$V_{CE} = -1.0\text{V}$ $I_C = -10\text{mA}$	100			

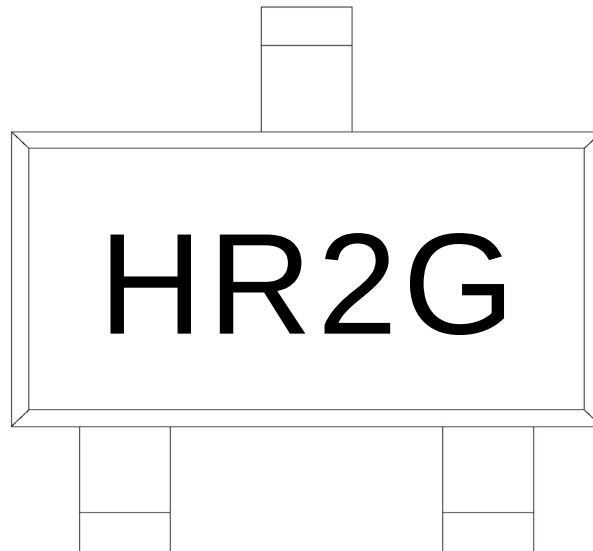
Collector to Emitter Saturation



SOT-323

单位: mm





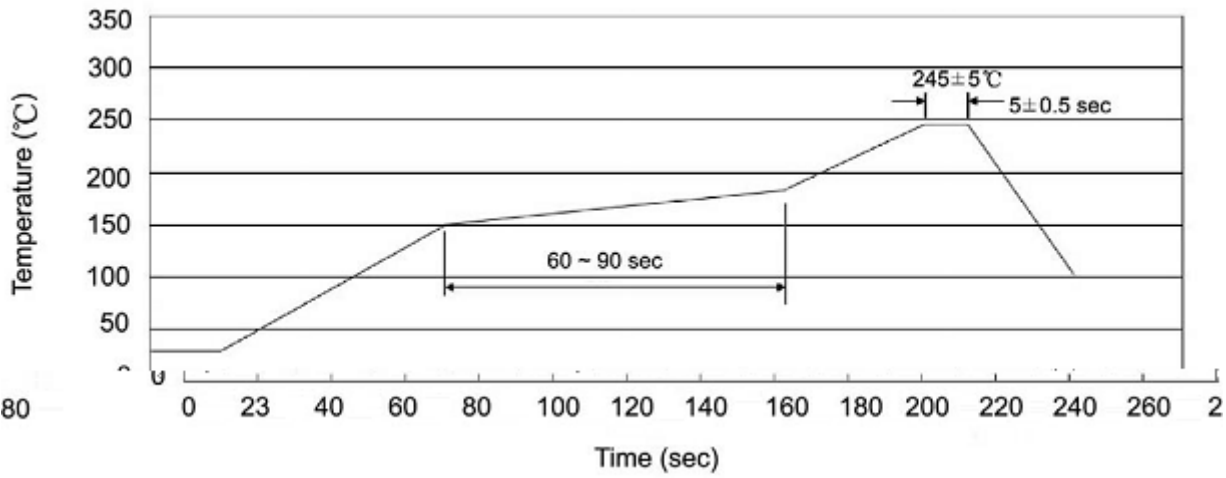
H

R2G

Note:

H: Company Code.

R2G: Product Type Code



Note:

- 1

25 150

60 90sec;

1.Preheating:25~150 , Time:60~90sec.
- 2

245 5

5 0.5sec;

2.Peak Temp.:245 5 , Duration:5 0.5sec.
- 3

2 10 /sec.

3. Cooling Speed: 2~10 /sec.

260 5

10 1 sec.

Temp.:260 5

Time:10 1 sec

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	只 卷盘	卷盘 盒	只 盒	盒 箱	只 箱		盒	箱
						"		